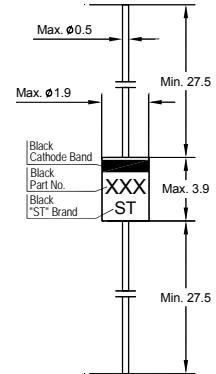


BZX79C

Silicon Planar Zener Diodes



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

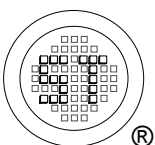
Parameter	Symbol	Value	Unit
Continuous Forward Current	I_F	250	mA
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	0.3 ¹⁾	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.5	V

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.



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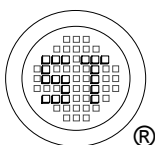
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BZX79C

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Type	Zener Voltage Range ¹⁾			Dynamic Resistance		Reverse Leakage Current	
	V_{ZT}		at I_{ZT}	Z_{ZT}	at I_{ZT}	I_R	at V_R
	Min. (V)	Max. (V)	(mA)	Max. (Ω)	(mA)	Max. (μA)	(V)
BZX79C2V4	2.2	2.6	5	100	5	100	1
BZX79C2V7	2.5	2.9	5	100	5	75	1
BZX79C3V0	2.8	3.2	5	95	5	50	1
BZX79C3V3	3.1	3.5	5	95	5	25	1
BZX79C3V6	3.4	3.8	5	90	5	15	1
BZX79C3V9	3.7	4.1	5	90	5	10	1
BZX79C4V3	4	4.6	5	90	5	5	1
BZX79C4V7	4.4	5	5	80	5	3	2
BZX79C5V1	4.8	5.4	5	60	5	2	2
BZX79C5V6	5.2	6	5	40	5	1	2
BZX79C6V2	5.8	6.6	5	10	5	3	4
BZX79C6V8	6.4	7.2	5	15	5	2	4
BZX79C7V5	7	7.9	5	15	5	1	5
BZX79C8V2	7.7	8.7	5	15	5	0.7	5
BZX79C9V1	8.5	9.6	5	15	5	0.5	6
BZX79C10	9.4	10.6	5	20	5	0.2	7
BZX79C11	10.4	11.6	5	20	5	0.1	8
BZX79C12	11.4	12.7	5	25	5	0.1	8
BZX79C13	12.4	14.1	5	30	5	0.1	8
BZX79C15	13.8	15.6	5	30	5	0.05	10.5
BZX79C16	15.3	17.1	5	40	5	0.05	11.2
BZX79C18	16.8	19.1	5	45	5	0.05	12.6
BZX79C20	18.8	21.2	5	55	5	0.05	14
BZX79C22	20.8	23.3	5	55	5	0.05	15.4
BZX79C24	22.8	25.6	5	70	5	0.05	16.8
BZX79C27	25.1	28.9	2	80	2	0.05	18.9
BZX79C30	28	32	2	80	2	0.05	21
BZX79C33	31	35	2	80	2	0.05	23.1
BZX79C36	34	38	2	90	2	0.05	25.2
BZX79C39	37	41	2	130	2	0.05	27.3
BZX79C43	40	46	2	150	2	0.05	30.1
BZX79C47	44	50	2	170	2	0.05	32.9
BZX79C51	48	54	2	180	2	0.05	35.7
BZX79C56	52	60	2	200	2	0.05	39.2
BZX79C62	58	66	2	215	2	0.05	43.4
BZX79C68	64	72	2	240	2	0.05	47.6
BZX79C75	70	79	2	255	2	0.05	52.5

¹⁾ Tested with pulses $t_p = 20\text{ ms}$.



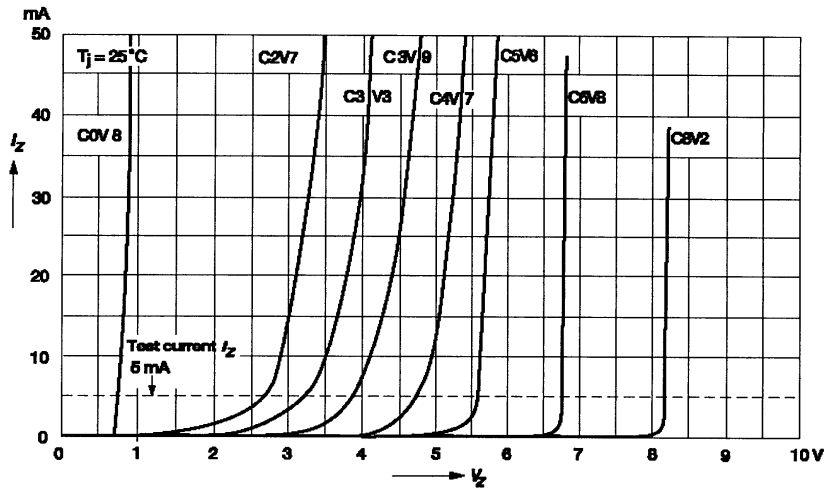
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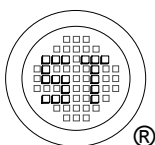
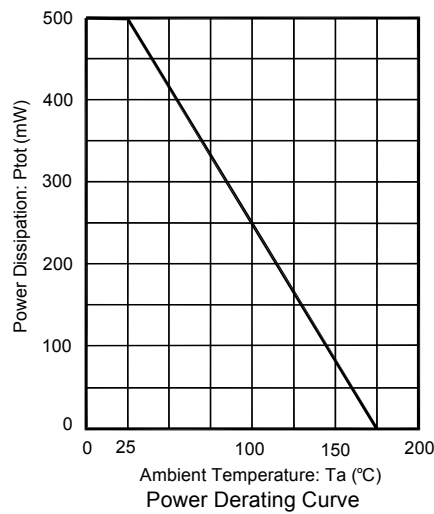
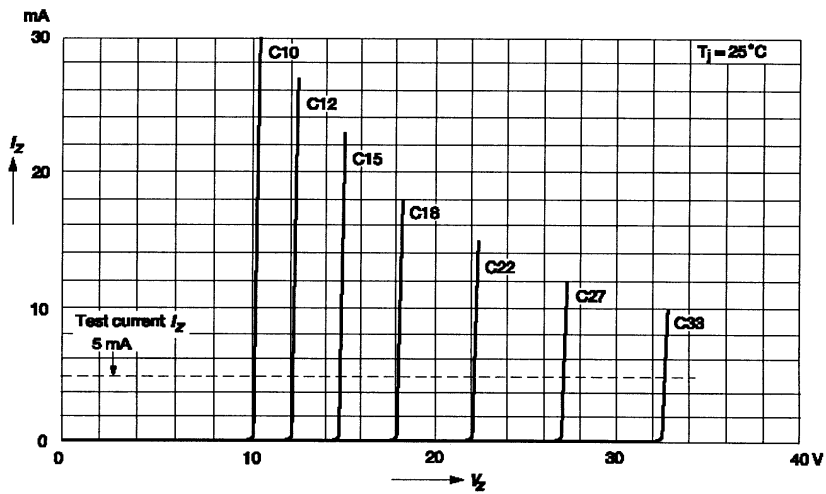
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Breakdown characteristics
at $T_j = \text{constant}$ (pulsed)



Breakdown characteristics
at $T_j = \text{constant}$ (pulsed)



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